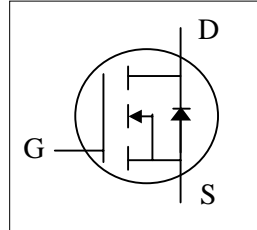




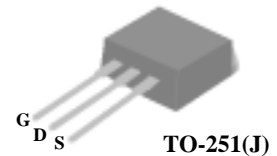
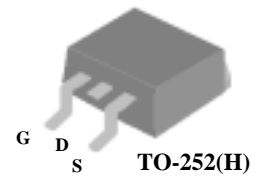
- Repetitive Avalanche Rated**
- Fast Switching Speed**
- Simple Drive Requirement**
- RoHS Compliant**



$BV_{DSS}$	700V
$R_{DS(ON)}$	4.4
$I_D$	2.5A

## Description

The TO-252 package is universally preferred for all commercial-industrial surface mount applications and suited for AC/DC converters. The through-hole version (AP03N70J) is available for low-profile applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	700	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D @ T_C=25$	Continuous Drain Current, $V_{GS}$ @ 10V	2.5	A
$I_D @ T_C=100$	Continuous Drain Current, $V_{GS}$ @ 10V	1.6	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	8	A
$P_D @ T_C=25$	Total Power Dissipation	54.3	W
	Linear Derating Factor	0.44	W/
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	31	mJ
$I_{AR}$	Avalanche Current	2.5	A
$T_{STG}$	Storage Temperature Range	-55 to 150	
$T_J$	Operating Junction Temperature Range	-55 to 150	

## Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case	Max. 2.3	/W
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	/W


**Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	700	-	-	V
$BV_{DSS}/T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1mA$	-	0.6	-	V/
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=1.6A$	-	-	4.4	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=1.6A$	-	2	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=600V, V_{GS}=0V$	-	-	10	$\mu A$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{DS}=480V, V_{GS}=0V$	-	-	100	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>3</sup>	$I_D=1A$	-	12	20	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	3	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	4	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>3</sup>	$V_{DD}=300V$	-	8.5	-	ns
$t_r$	Rise Time	$I_D=2.5A$	-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	19	-	ns
$t_f$	Fall Time	$R_D=120\Omega$	-	8	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	590	950	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	50	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0MHz$	-	6	-	pF
$R_g$	Gate Resistance	$f=1.0MHz$	-	3.4	5.1	

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>3</sup>	$I_S=2.5A, V_{GS}=0V$	-	-	1.5	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=2.5A, V_{GS}=0V,$	-	407	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	2110	-	nC

**Notes:**

1. Pulse width limited by safe operating area.
2. Starting  $T_j=25^\circ\text{C}$ ,  $V_{DD}=50V$ ,  $L=10mH$ ,  $R_G=25\Omega$ ,  $I_{AS}=2.5A$ .
3. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

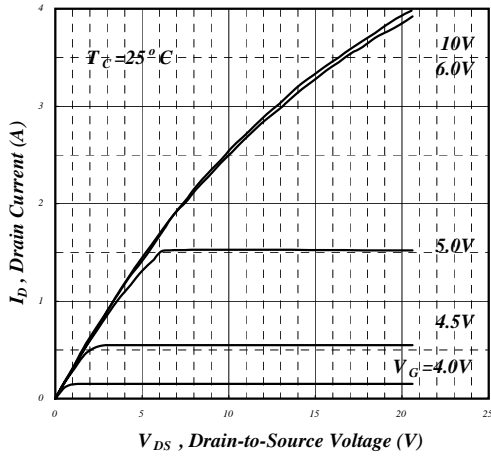


Fig 1. Typical Output Characteristics

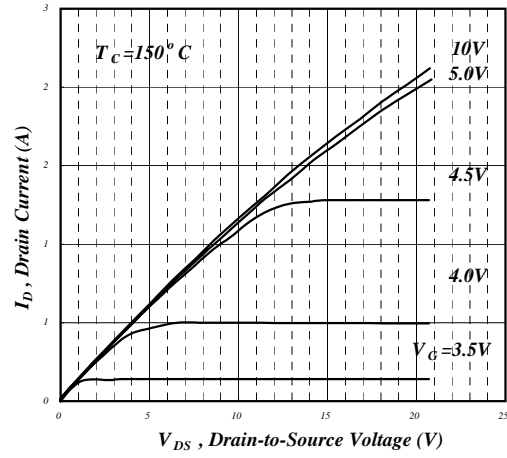


Fig 2. Typical Output Characteristics

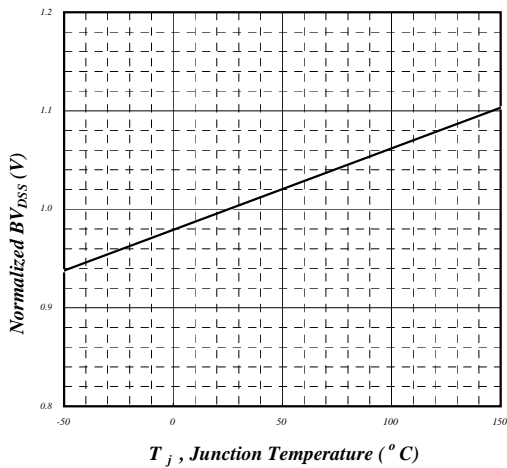


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

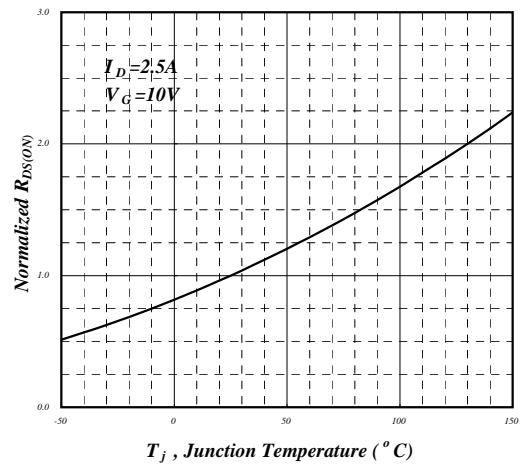


Fig 4. Normalized On-Resistance v.s. Junction Temperature

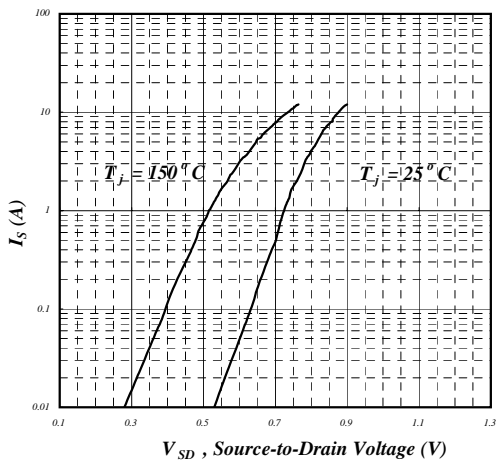


Fig 5. Forward Characteristic of Reverse Diode

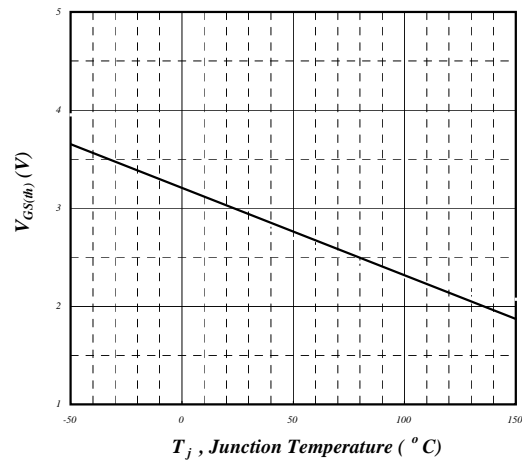


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

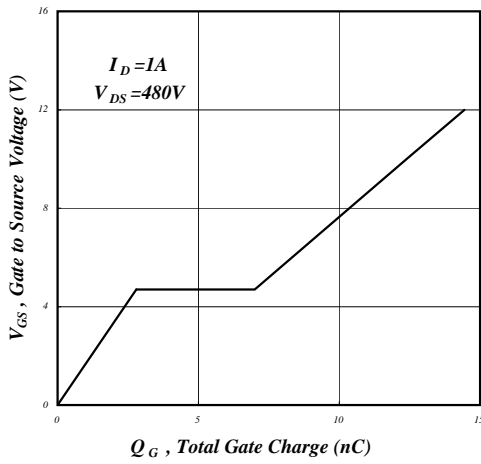


Fig 7. Gate Charge Characteristics

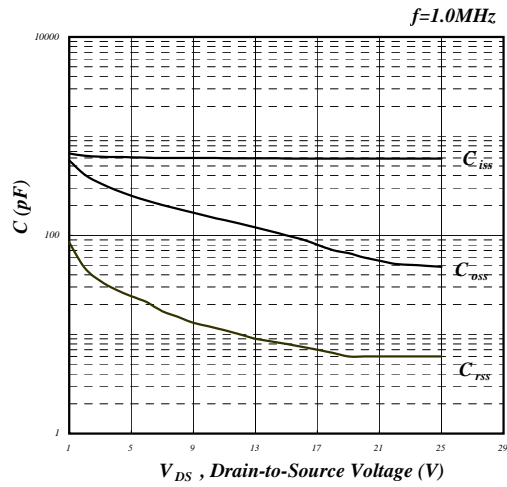


Fig 8. Typical Capacitance Characteristics

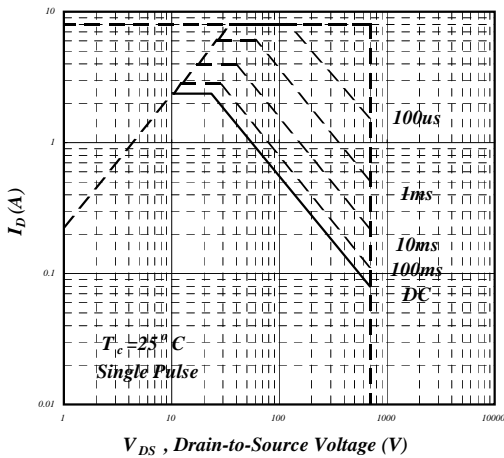


Fig 9. Maximum Safe Operating Area

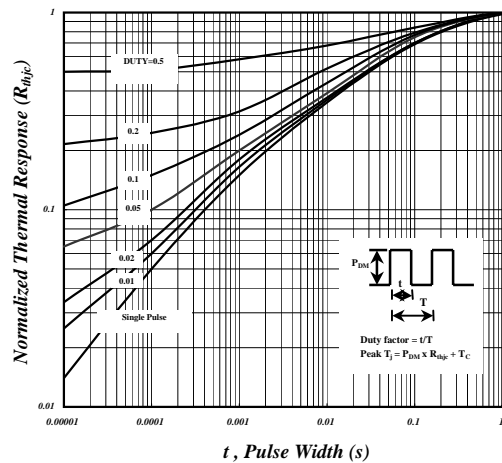


Fig 10. Effective Transient Thermal Impedance

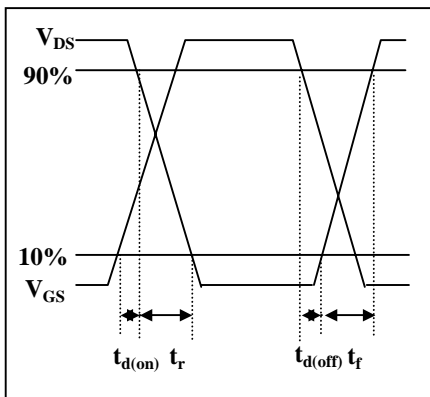


Fig 11. Switching Time Waveform

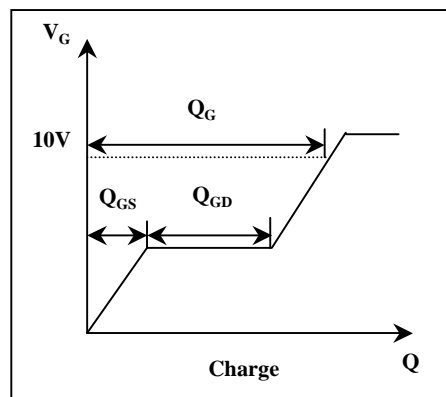


Fig 12. Gate Charge Waveform